

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = 25^\circ\text{C}$
20V	56m Ω @ $V_{GS} = 4.5\text{V}$	2.8A
	65m Ω @ $V_{GS} = 2.5\text{V}$	2.6A
	93m Ω @ $V_{GS} = 1.8\text{V}$	2.2A
	140m Ω @ $V_{GS} = 1.5\text{V}$	1.8A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 standards for High Reliability**

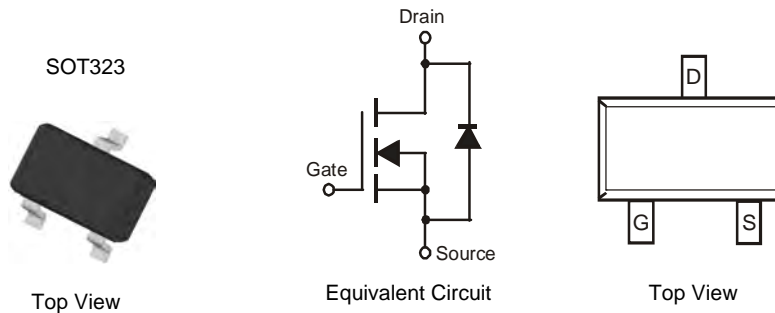
Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Alloy42 leadframe.
Solderable per MIL-STD-202, Method 208
- Weight: 0.027 grams (approximate)

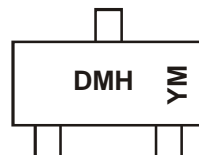


Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2065UW-7	SOT323	3000/Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



DMH = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = 25°C T _A = 70°C	I _D	2.8 2.3	A
	t<10s	T _A = 25°C T _A = 70°C	I _D	3.1 2.6	A
Continuous Drain Current (Note 5) V _{GS} = 1.8V	Steady State	T _A = 25°C T _A = 70°C	I _D	2.2 1.7	A
	t<10s	T _A = 25°C T _A = 70°C	I _D	2.4 1.9	A
Pulsed Drain Current (10us pulse, duty cycle=1%)			I _{DM}	30	A
Maximum Body Diode Forward Current (Note 4)			I _S	1.2	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 4)		P _D	0.43	W
Thermal Resistance, Junction to Ambient (Note 4)	Steady state	R _{θJA}	296	°C/W
	t<10s		252	°C/W
Total Power Dissipation (Note 5)		P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	178	°C/W
	t<10s		151	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current @T _c = 25°C	I _{DSS}	-	-	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±1	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.35	-	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	52	56	mΩ	V _{GS} = 4.5V, I _D = 2A
		-	59	65		V _{GS} = 2.5V, I _D = 2A
		-	60	93		V _{GS} = 1.8V, I _D = 1A
		-	75	140		V _{GS} = 1.5V, I _D = 0.5A
		-	7	-		V _{DS} = 5V, I _D = 3.8A
Forward Transfer Admittance	Y _{fs}	-	7	-	S	V _{DS} = 5V, I _D = 3.8A
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	400.0	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	73.8	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	65.6	-	pF	
Total Gate Charge	Q _g	-	5.4	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6A
Gate-Source Charge	Q _{gs}	-	0.7	-	nC	
Gate-Drain Charge	Q _{gd}	-	1.4	-	nC	
Turn-On Delay Time	t _{D(on)}	-	3.5	-	ns	V _{DD} = 10V, V _{GS} = 5V, R _L = 1.7Ω, R _G = 6Ω,
Turn-On Rise Time	t _r	-	9.7	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	23.8	-	ns	
Turn-Off Fall Time	t _f	-	7.2	-	ns	

- Notes: 4. Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

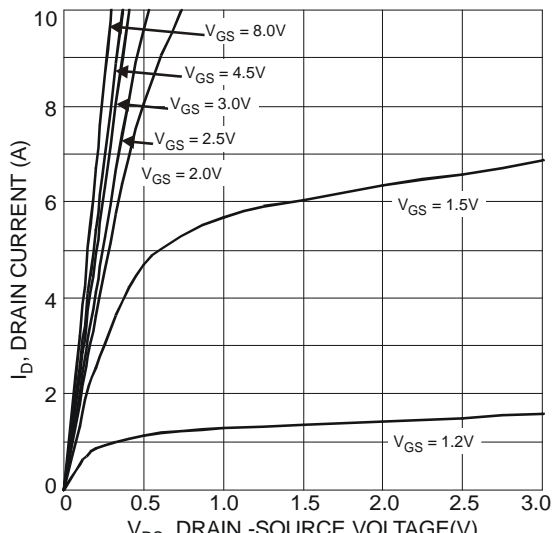


Fig. 1 Typical Output Characteristics

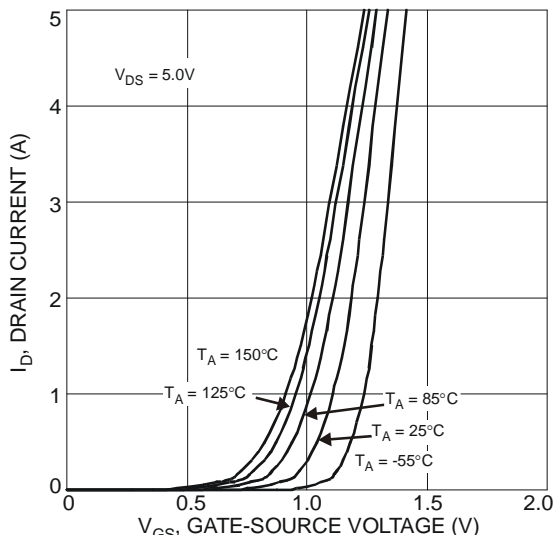


Fig. 2 Typical Transfer Characteristics

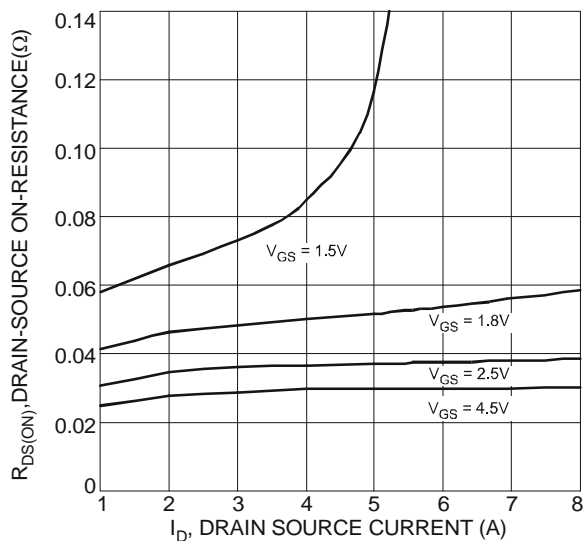


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

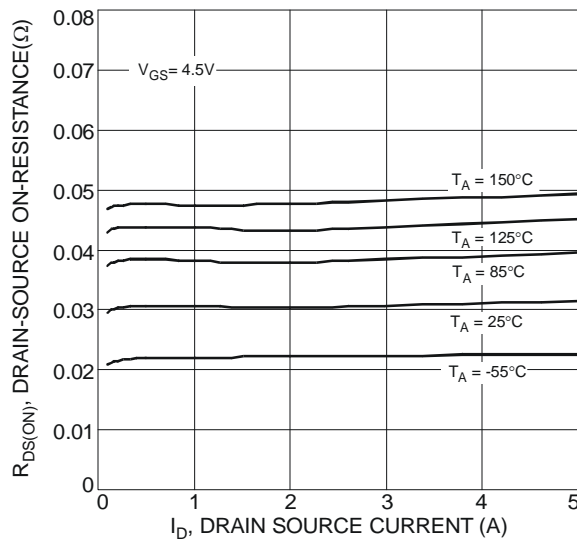


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

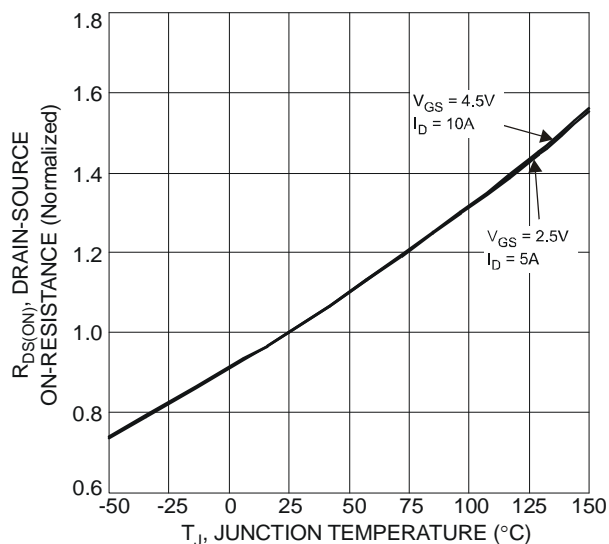


Fig. 5 On-Resistance Variation with Temperature

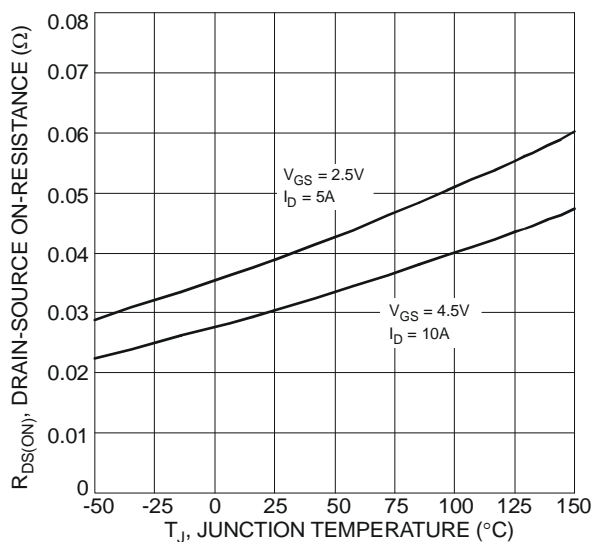


Fig. 6 On-Resistance Variation with Temperature

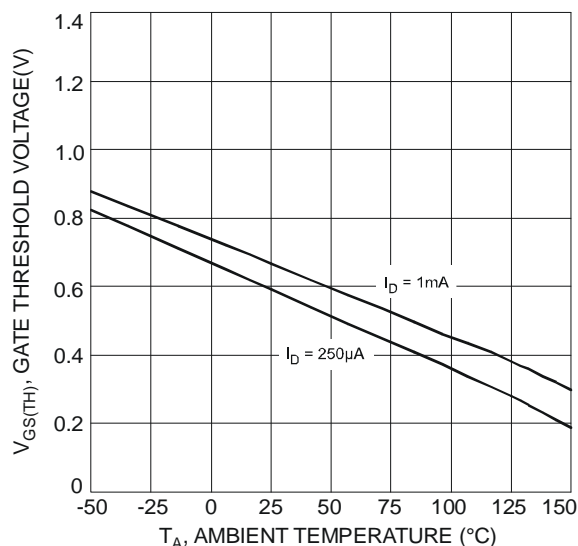


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

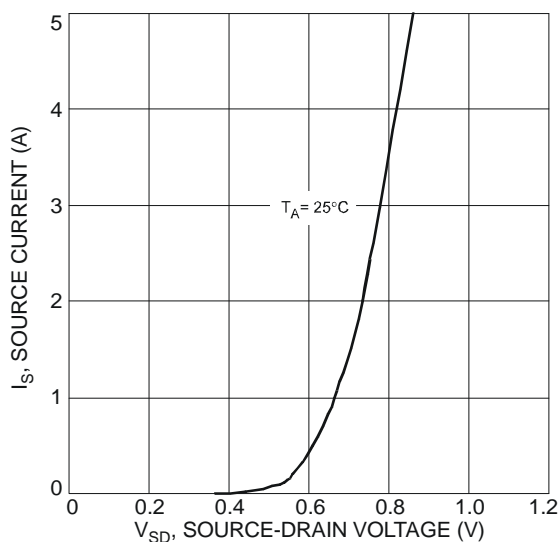


Fig. 8 Diode Forward Voltage vs. Current

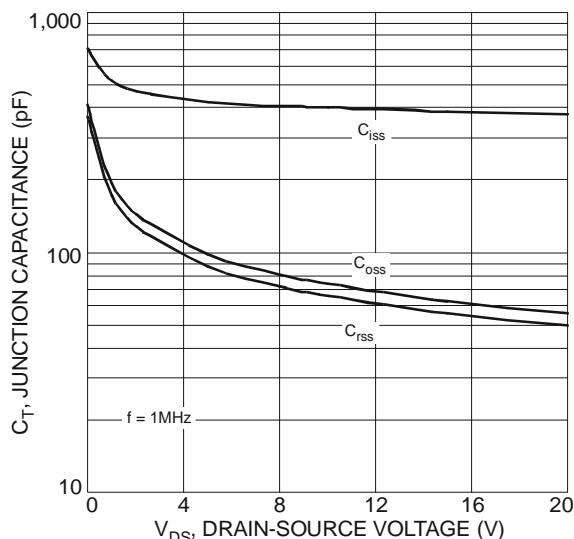


Fig. 9 Typical Junction Capacitance

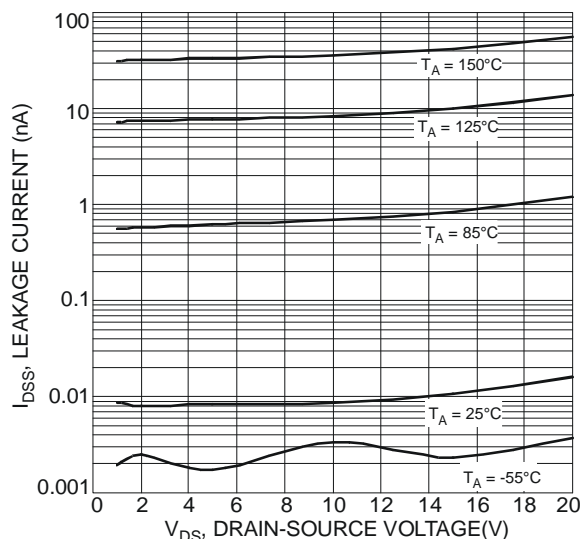


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

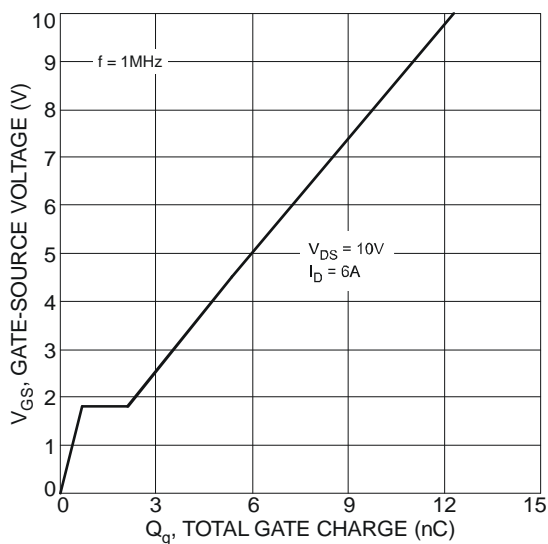


Fig. 11 Gate-Charge Characteristics

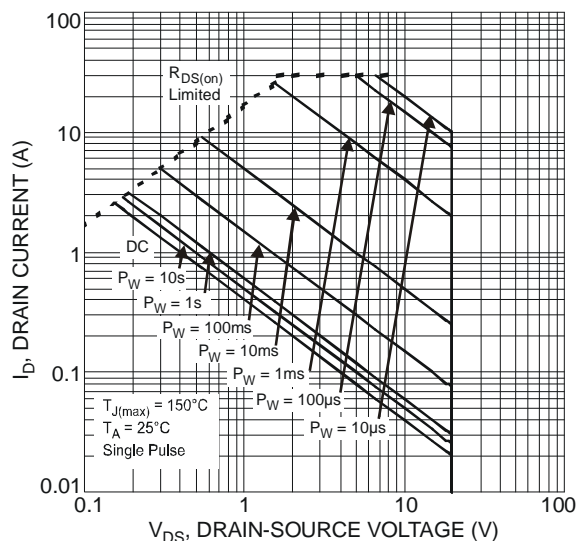
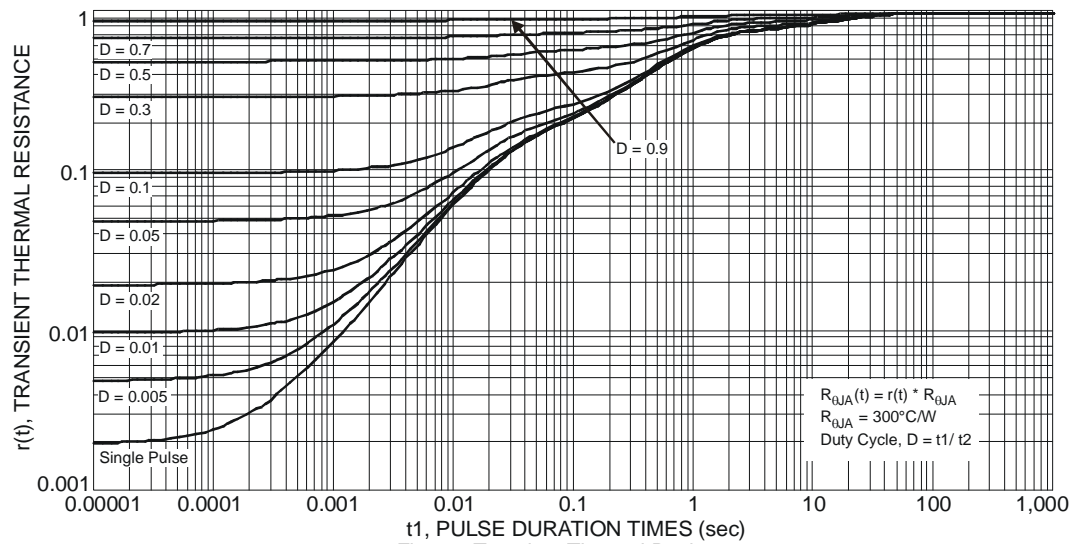
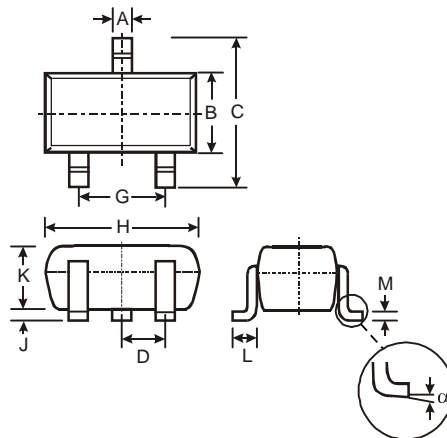


Fig. 12 SOA, Safe Operation Area

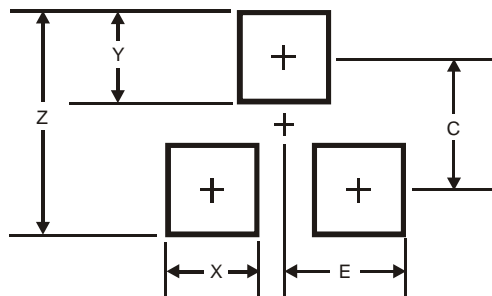


Package Outline Dimensions



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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